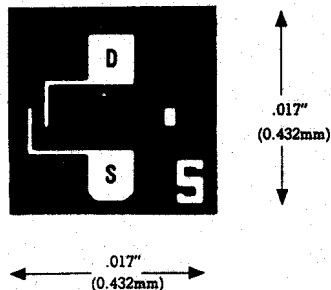


CHIP NUMBER

FN2.2



Die Size: .17 x .17 (mils)
0.432 x 0.432(mm)
3.5 x 4 (mils)
Pad Size: 0.089 x 0.102(mm)
GATE-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000
Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- a) the die be eutectically mounted with gold silicon preform 98/2%.
- b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVGSS	-30	-60	-80	V	V _{DS} = 0V, I _G = 1μA
I _{DSS}	0.02	0.25	1.0	mA	V _{DS} = 10V, V _{GS} = 0
g _{fs}	80	250	350	μmho	V _{DS} = 10V, V _{GS} = 0
I _{GSS}		-0.3	-10	pA	V _{GS} = -20V, V _{DS} = 0
V _{GS(off)}	-0.5	-2.0	-6.0	V	V _{DS} = 10V, I _D = 1nA
C _{rss}	.7	0.8	1.0	pF	V _{DS} = 15V, V _{GS} = 0, f = 1MHz
C _{iss}	1.7	2.0	2.5	pF	V _{DS} = 15V, V _{GS} = 0, f = 1MHz
ē _n		45	150	nV/√Hz	V _{DG} = 10V, I _D = 50μA, f = 100Hz

TYPICAL DEVICE TYPES: 2N4117A, 2N4119A, 2N3452, 2N5902-2N5909

CHIP TYPE FN2.2

